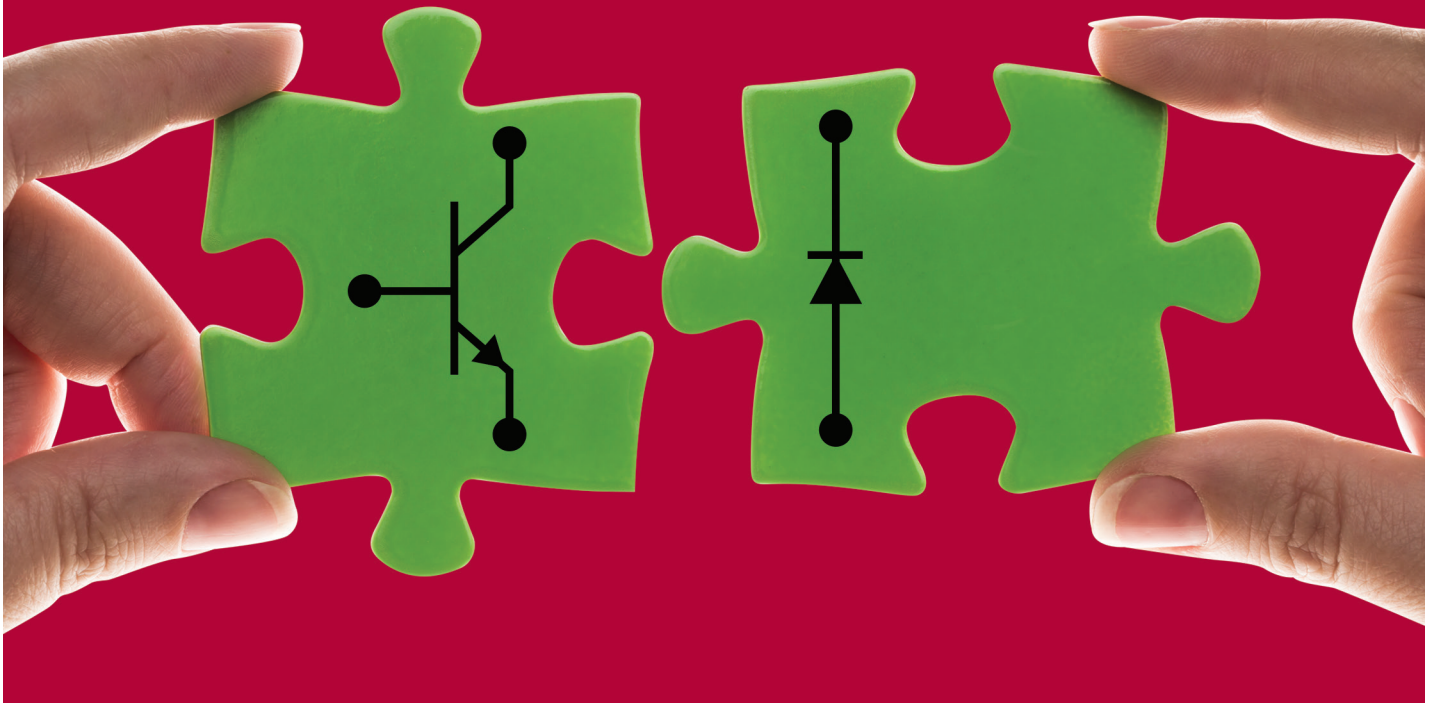


Trench Field Stop IGBT and FRED Pt[®] Gen4 Diode

The Ideal Match

Trench Field
Stop IGBT

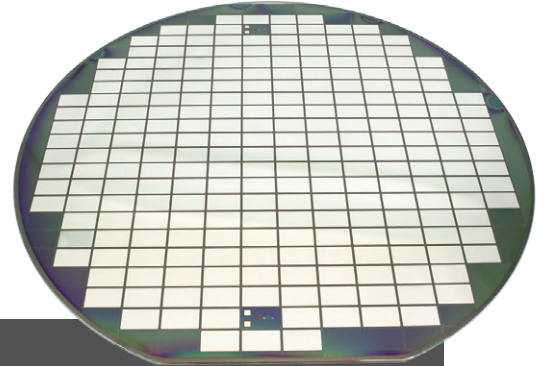
FRED Pt[®]
Gen4 Diode



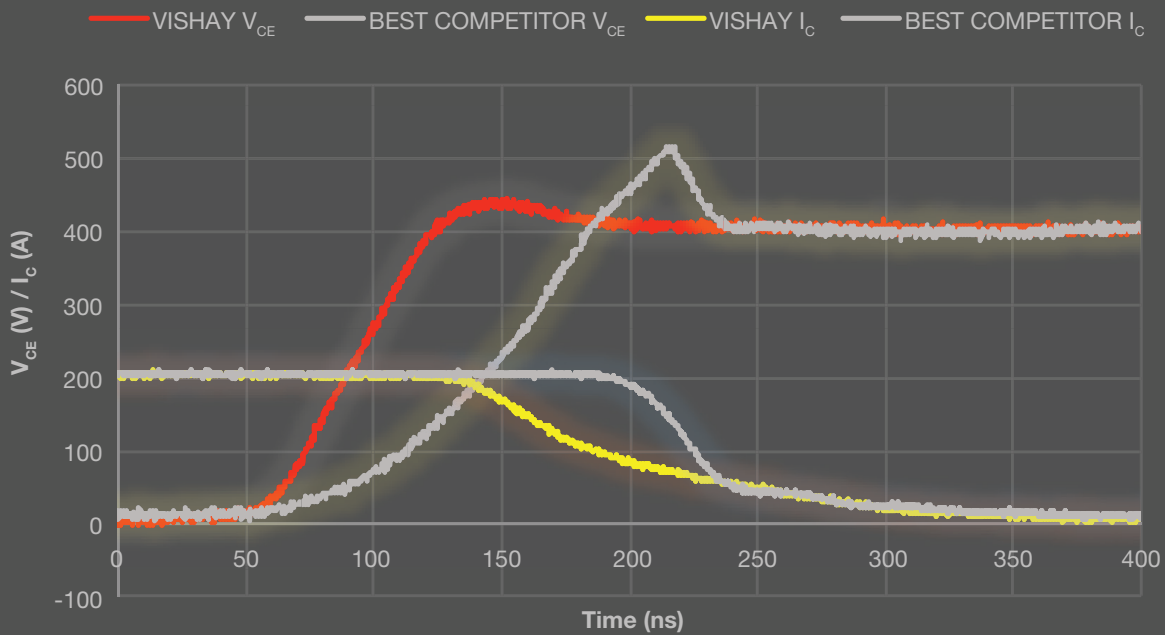


New Trench IGBT and FRED Pt[®] Gen4 Chips

- Both platforms are available as sawn or unsawn wafers
- Trench construction: small IGBT chips feature low $V_{CE(on)}$
- Thin wafers: Low R_{th} and ohmic losses
- Spike-free IGBT turn-off and ultrasoft recovery diode combined for maximum performance
- IGBT and diodes are designed for matching operation in applications and are offered as a kit on request
- Trench PT devices are optimized for low switching frequencies to 1 kHz
- Trench FS IGBTs offer 6 μ s short-circuit rating and high operating temperatures to +175 °C
- Feature collector current ratings from 30 A to 240 A
- Breakdown voltages of 600 V and 650 V for increased reliability



200 A, 600 V IGBT Chip Turn-Off



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